To all our customers

Regarding the change of names mentioned in the document, such as Mitsubishi Electric and Mitsubishi XX, to Renesas Technology Corp.

The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note : Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

2002.9.3 Ver. 0.0

M5M5W817KT - 70HI

8388608-BIT (524288-WORD BY 16-BIT / 10485776-WORD BY 8-BIT) CMOS STATIC RAM

DESCRIPTION

The M5M5W817KT is a family of low voltage 8Mbit static RAMs organized as 524288-words by 16-bit / 1048576-words by 8-bit, fabricated by Mitsubishi's high-performance 0.18µm CMOS technology.

The M5M5W817KT is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives.

The M5M5W817KT is packaged in a 52pin-µTSOP with the outline of 10.79mm x 10.49mm, and pin pitch of 0.40mm. It gives the best solution for a compaction of mounting area as well as flexibility of wiring pattern of printed circuit boards.

The operating temperature range is -40 ~ +85°C

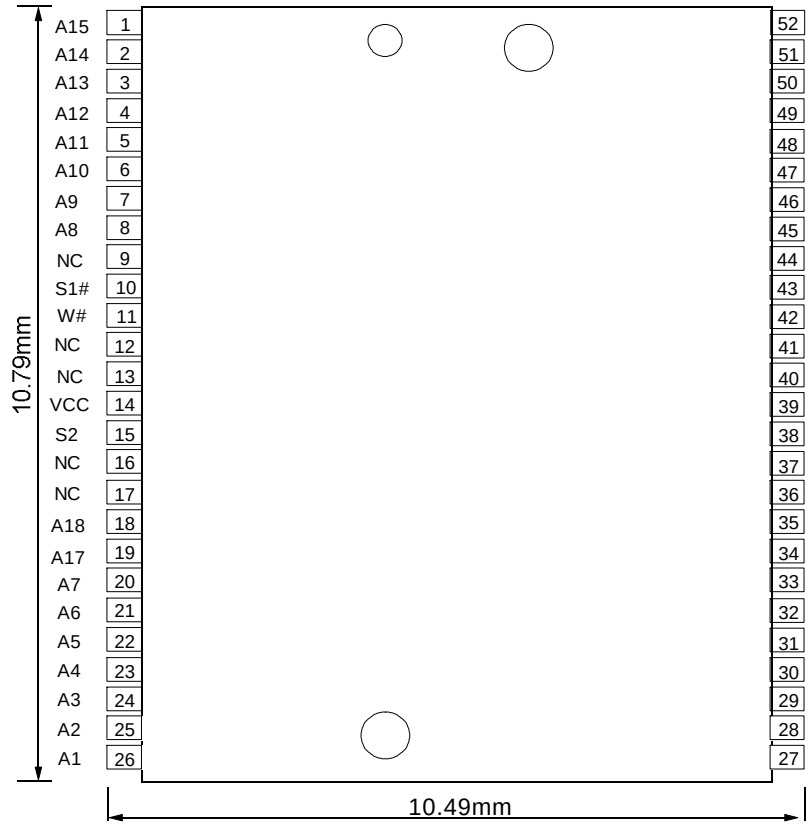
FEATURES

- Single 2.7~3.6V power supply
- Small stand-by current: 0.1µA (2.0V, typ.)
- No clocks, No refresh
- Data retention supply voltage =2.0~3.6V
- All inputs and outputs are TTL compatible.
- Easy memory expansion by S1#, S2, BC1# and BC2#
- Common Data I/O
- Three-state outputs: OR-tie capability
- OE prevents data contention in the I/O bus
- Byte function (x8 mode) available by Byte# & A-1.
- Process technology: 0.18µm CMOS
- Package: 52pin 10.79mm x 10.49mm µTSOP
  [0.4mm pin pitch]

Operating temperature	Part name	Power Supply	Access time max.	Stand-by current * Typical 25ºC	Stand-by current * Typical 40ºC	Stand-by current Ratings (max.) 25ºC	Stand-by current Ratings (max.) 40ºC	Stand-by current Ratings (max.) 70ºC	Stand-by current Ratings (max.) 85ºC	Active current Icc1 (3.3V, Typ.)
-40 ~ +85°C	M5M5W817KT -70HI	2.7 ~ 3.6V	70ns	1.0	1.2	5	8	20	40	30mA (10MHz) 5mA (1MHz)

* Typical parameter indicates the value for the center of distribution, and not 100% tested.

PIN CONFIGURATION



Pin	Function
A0 ~ A18	Address input
DQ1 ~ DQ16	Data input / output
S1#	Chip select input 1
S2	Chip select input 2
W#	Write control input
OE#	Output enable input
BC1#	Lower Byte (DQ1 ~ 8)
BC2#	Upper Byte (DQ9 ~ 16)
BYTE#	Byte (x8 mode) enable input
Vcc	Power supply
GND	Ground supply

Outline: 52PTG-A
N C : No Connection

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FUNCTION

The M5M5W817KT is organized as 524288-words by 16-bit / 1048576-words by 8-bit. These devices operate on a single +2.7~3.6V power supply, and are directly TTL compatible to both input and output. Its fully static circuit needs no clocks and no refresh, and makes it useful.

The operation mode are determined by a combination of the device control inputs BC1# , BC2# , S1#, S2 , W#, OE# and BYTE#. Each mode is summarized in the function table.

A write operation is executed whenever the low level W# overlaps with the low level BC1# and/or BC2# and the low level S1# and the high level S2. The address (A-1~A18 : Byte mode, A0~A18 : Word mode) must be set up before the write cycle and must be stable during the entire cycle.

A read operation is executed by setting W# at a high level and OE# at a low level while BC1# and/or BC2# and S1#and S2 are in an active state (S1#=L, S2=H).

When setting BYTE# at a low level, the function will be in the x8 mede, which is, DQ1-8 are available and DQ9-16 are not available. In the x8 mode, A-1 is used as the additional address. During the active function for x8 mode, BC1# BC2# must be low level.

When setting BC1# and BC2# at a high level or S1# at a high level or S2 at a low level, the chips are in a non-selectable mode in which both reading and writing are disabled.

In this mode, the output stage is in a high-impedance state, allowing OR-tie with other chips and memory expansion by BC1#, BC2# and S1#, S2.

The power supply current is reduced as low as 0.1µA (25°C, typical), and the memory data can be held at +2.0V power supply, enabling battery back-up operation during power failure or power-down operation in the non-selected mode.

FUNCTION TABLE

S1#	S2	BYTE#	BC1#	BC2#	W#	OE#	Mode	DQ1~8	DQ9~15	DQ16	Icc
H	H	H or L	X	X	X	X	Non selection	High-Z	High-Z	High-Z	Standby
X	L	H or L	X	X	X	X	Non selection	High-Z	High-Z	High-Z	Standby
X	X	H	H	H	X	X	Non selection	High-Z	High-Z	High-Z	Standby
L	H	H	L	H	L	X	Write	Din	High-Z	High-Z	Active
L	H	H	L	H	H	L	Read	Dout	High-Z	High-Z	Active
L	H	H	L	H	H	H	-------	High-Z	High-Z	High-Z	Active
L	H	H	H	L	L	X	Write	High-Z	Din	Din	Active
L	H	H	H	L	H	L	Read	High-Z	Dout	Dout	Active
L	H	H	H	L	H	X	-------	High-Z	High-Z	High-Z	Active
L	H	H	L	L	L	X	Write	Din	Din	Din	Active
L	H	H	L	L	H	L	Read	Dout	Dout	Dout	Active
L	H	H	L	L	H	X	-------	High-Z	High-Z	High-Z	Active
L	H	L	L	L	L	X	Write	Din	High-Z	A-1	Active
L	H	L	L	L	H	L	Read	Dout	High-Z	A-1	Active
L	H	L	L	L	H	H	-------	High-Z	High-Z	A-1	Active

Note1 : "H" and "L" in this table mean V_{IH} and V_{IL}, respectively.
Note2 : "X" in this table should be "H" or "L".

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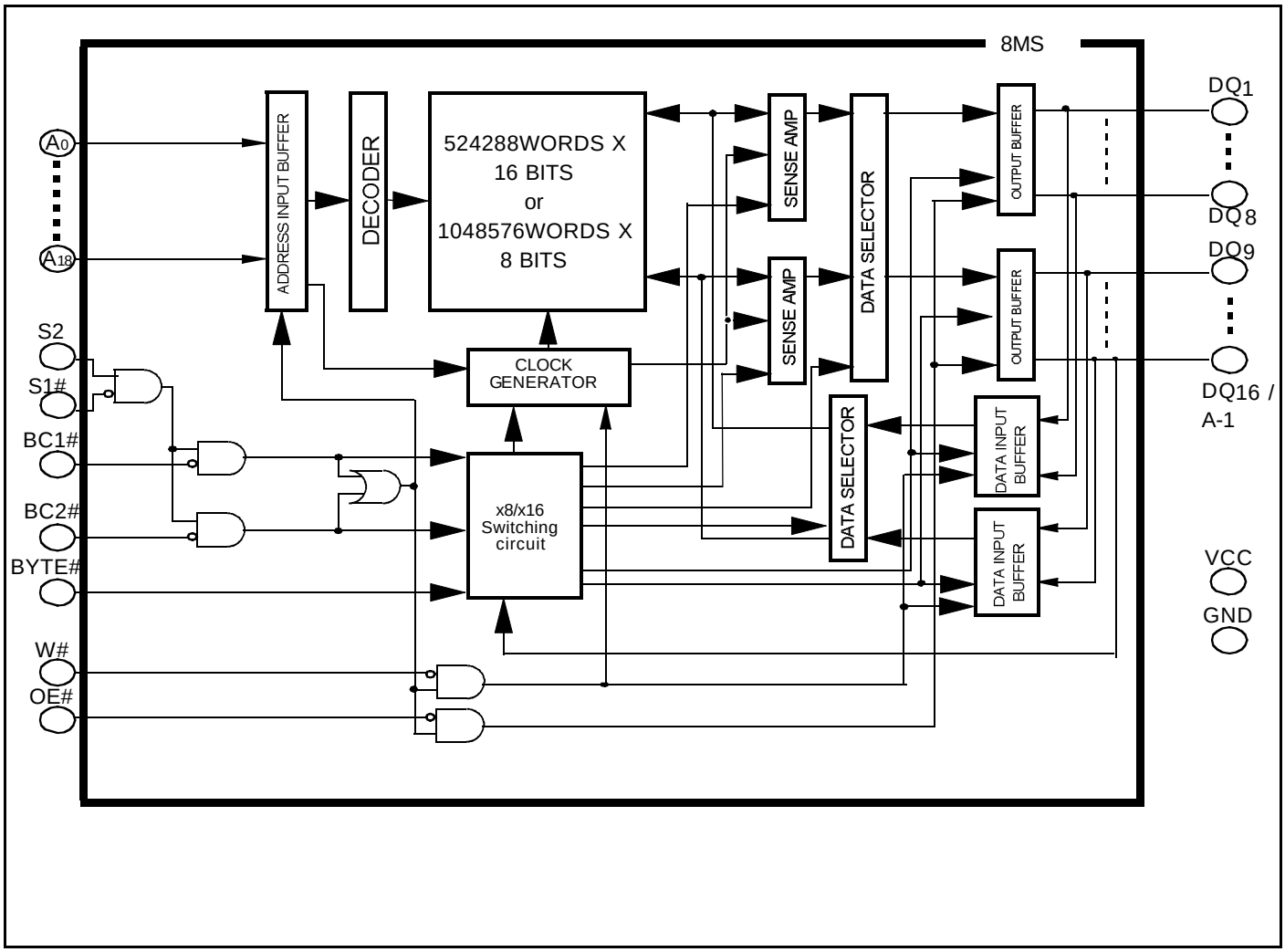
8388608-BIT (524288-WORD BY 16-BIT / 10485776-WORD BY 8-BIT) CMOS STATIC RAM

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Units
V_{CC}	Supply voltage	With respect to GND	- 0.3* ~ +4.6	V
V_I	Input voltage	With respect to GND	- 0.3* ~ Vcc + 0.3 (max. 4.6V)	
V_O	Output voltage	With respect to GND	0 ~ Vcc	
P_d	Power dissipation	Ta = 25°C	700	mW
T_a	Operating temperature		-40 ~ +85	°C
T_{stg}	Storage temperature		- 65 ~ +150	°C

* -3.0V in case of AC (Pulse width ≤ 30ns)

DC ELECTRICAL CHARACTERISTICS (Ta=-40~85°C Vcc=2.7V~3.6V,unless otherwise noted)

Symbol	Parameter	Conditions		Limits Min	Limits Typ	Limits Max	Units
V_{IH}	High-level input voltage			2.2		Vcc+0.2V	V
V_{IL}	Low-level input voltage			- 0.2 *		0.6	
V_{OH}	High-level output voltage	I_{OH}= - 0.5mA		2.4			
V_{OL}	Low-level output voltage	I_{OL}= 2.0mA				0.4	
I_I	Input leakage current	V_I =0 ~ Vcc				±1	µA
I_O	Output leakage current	BC1# and BC2#=VIH or S1#=VIH or S2=VIL or OE#=VIH, VI/O=0 ~ Vcc				±1	
Icc1	Active supply current (AC,MOS level)	BC1# and BC2# ≤ 0.2V, S1# ≤ 0.2V, S2 ≥Vcc-0.2V other inputs ≤ 0.2V or ≥ Vcc-0.2V Output - open (duty 100%)	f= 10MHz	-	30	50	mA
			f= 1MHz	-	5	15	
Icc2	Active supply current (AC,TTL level)	BC1# and BC2#=VIL , S1#=VIL ,S2=VIH other pins =VIH or VIL Output - open (duty 100%)	f= 10MHz	-	30	50	
			f= 1MHz	-	5	15	
Icc3	Stand by supply current (AC,MOS level)	(1) S1# ≥ Vcc - 0.2V and S2 ≥ Vcc - 0.2V, BYTE# ≥ Vcc - 0.2V or ≤ 0.2V, other inputs = 0 ~ Vcc	~ +25°C	-	1.0	5	µA
		(2) S2 ≤ 0.2V, BYTE# ≥ Vcc - 0.2V or ≤ 0.2V, other inputs = 0 ~ Vcc	~ +40°C	-	1.2	8	
		(3) BC1# and BC2# ≥ Vcc - 0.2V S1# ≤ 0.2V, S2 ≥ Vcc - 0.2V BYTE# ≥ Vcc - 0.2V or ≤ 0.2V, other inputs = 0 ~ Vcc	~ +70°C	-	-	20	
			~ +85°C	-	-	40	
Icc4	Stand by supply current (AC,TTL level)	BC1# and BC2# =VIH or S1# =VIH or S2=VIL BYTE# ≥ Vcc - 0.2V or ≤ 0.2V, Other inputs= 0 ~ Vcc		-	-	2.0	mA

* -1.0V in case of AC (Pulse width ≤ 30ns)

Note 3: Direction for current flowing into IC is indicated as positive (no mark)
Note 4: Typical parameter indicates the value for the center of distribution at 3.0V, and not 100% tested.

CAPACITANCE (Ta=-40~+85°C Vcc=2.7V~3.6V,unless otherwise noted)

Symbol	Parameter	Conditions	Limits Min	Limits Typ	Limits Max	Units
C_I	Input capacitance	V_I=GND, V_I=25mVrms, f=1MHz			10	pF
C_O	Output capacitance	V_O=GND, V_O=25mVrms, f=1MHz			10	

AC ELECTRICAL CHARACTERISTICS (Ta=-40~+85ºC, Vcc=2.7V~3.6V,unless otherwise noted)

(1) TEST CONDITIONS

Supply voltage	2.7~3.6V
Input pulse	V_{IH}=2.7V, V_{IL}=0.2V
Input rise time and fall time	5ns
Reference level	V_{OH}=V_{OL}=1.5V Transition is measured ±200mV from steady state voltage.(for ten,tdis)
Output loads	Fig.1,CL=30pF CL=5pF (for ten,tdis)

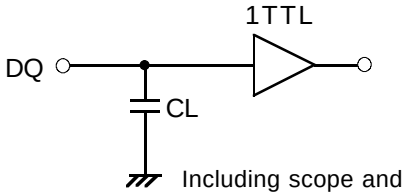


Fig.1 Output load

(2) READ CYCLE

Symbol	Parameter	Limits 70HI Min	Limits 70HI Max	Units
t_{CR}	Read cycle time	70		ns
t_a(A)	Address access time		70	ns
t_a(S1)	Chip select 1 access time		70	ns
t_a(S2)	Chip select 2 access time		70	ns
t_a(BC1)	Byte control 1 access time		70	ns
t_a(BC2)	Byte control 2 access time		70	ns
t_a(OE)	Output enable access time		35	ns
t_{dis}(S1)	Output disable time after S1# high		25	ns
t_{dis}(S2)	Output disable time after S2 low		25	ns
t_{dis}(BC1)	Output disable time after BC1# high		25	ns
t_{dis}(BC2)	Output disable time after BC2# high		25	ns
t_{dis}(OE)	Output disable time after OE# high		25	ns
t_{en}(S1)	Output enable time after S1# low	10		ns
t_{en}(S2)	Output enable time after S2 high	10		ns
t_{en}(BC1)	Output enable time after BC1# low	5		ns
t_{en}(BC2)	Output enable time after BC2# low	5		ns
t_{en}(OE)	Output enable time after OE# low	5		ns
t_V(A)	Data valid time after address	10		ns

(3) WRITE CYCLE

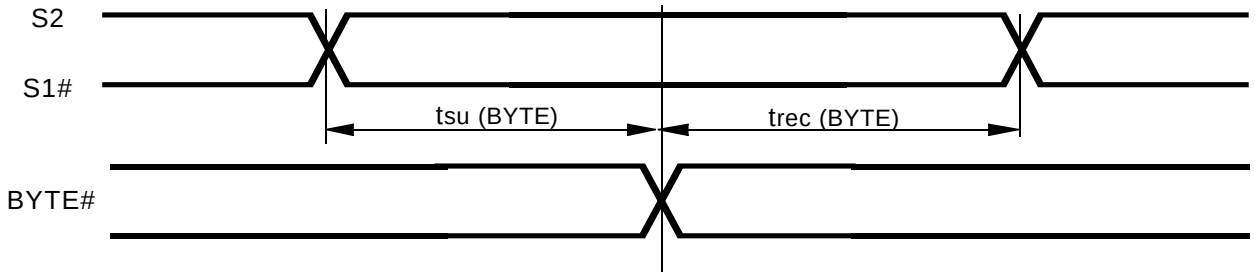
Symbol	Parameter	Limits 70HI Min	Limits 70HI Max	Units
t_{CW}	Write cycle time	70		ns
t_w(W)	Write pulse width	55		ns
t_{su}(A)	Address setup time	0		ns
t_{su}(A-WH)	Address setup time with respect to W#	65		ns
t_{su}(BC1)	Byte control 1 setup time	65		ns
t_{su}(BC2)	Byte control 2 setup time	65		ns
t_{su}(S1)	Chip select 1 setup time	65		ns
t_{su}(S2)	Chip select 2 setup time	65		ns
t_{su}(D)	Data setup time	35		ns
t_h(D)	Data hold time	0		ns
t_{rec}(W)	Write recovery time	0		ns
t_{dis}(W)	Output disable time from W# low		25	ns
t_{dis}(OE)	Output disable time from OE# high		25	ns
t_{en}(W)	Output enable time from W# high	5		ns
t_{en}(OE)	Output enable time from OE# low	5		ns

(4) Byte# function

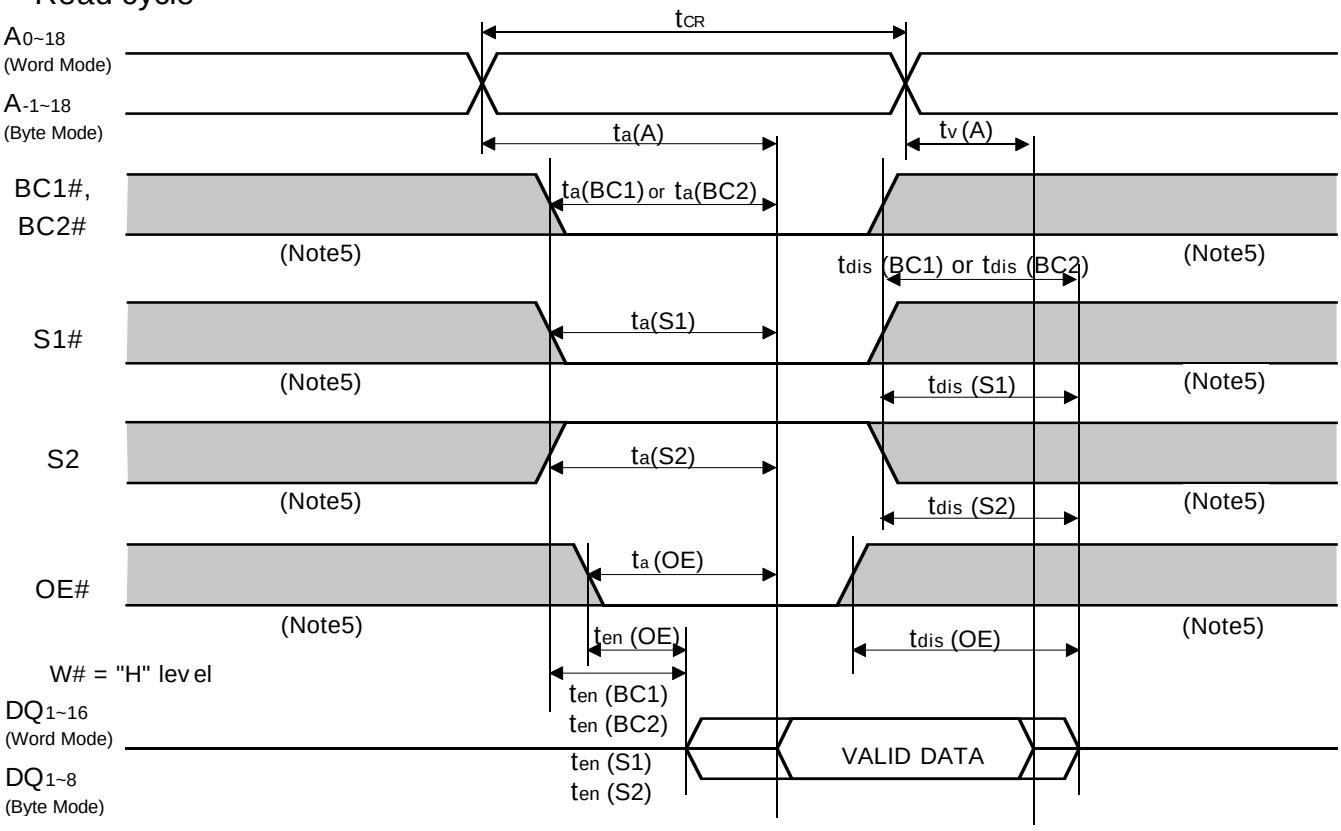
Symbol	Parameter	Test conditions	Limits			Units
			Min	Typ	Max	
$t_{su\ (BYTE)}$	BYTE# set up time		5			ms
$t_{rec\ (BYTE)}$	BYTE# recovery time		5			ms

(5) TIMING DIAGRAMS

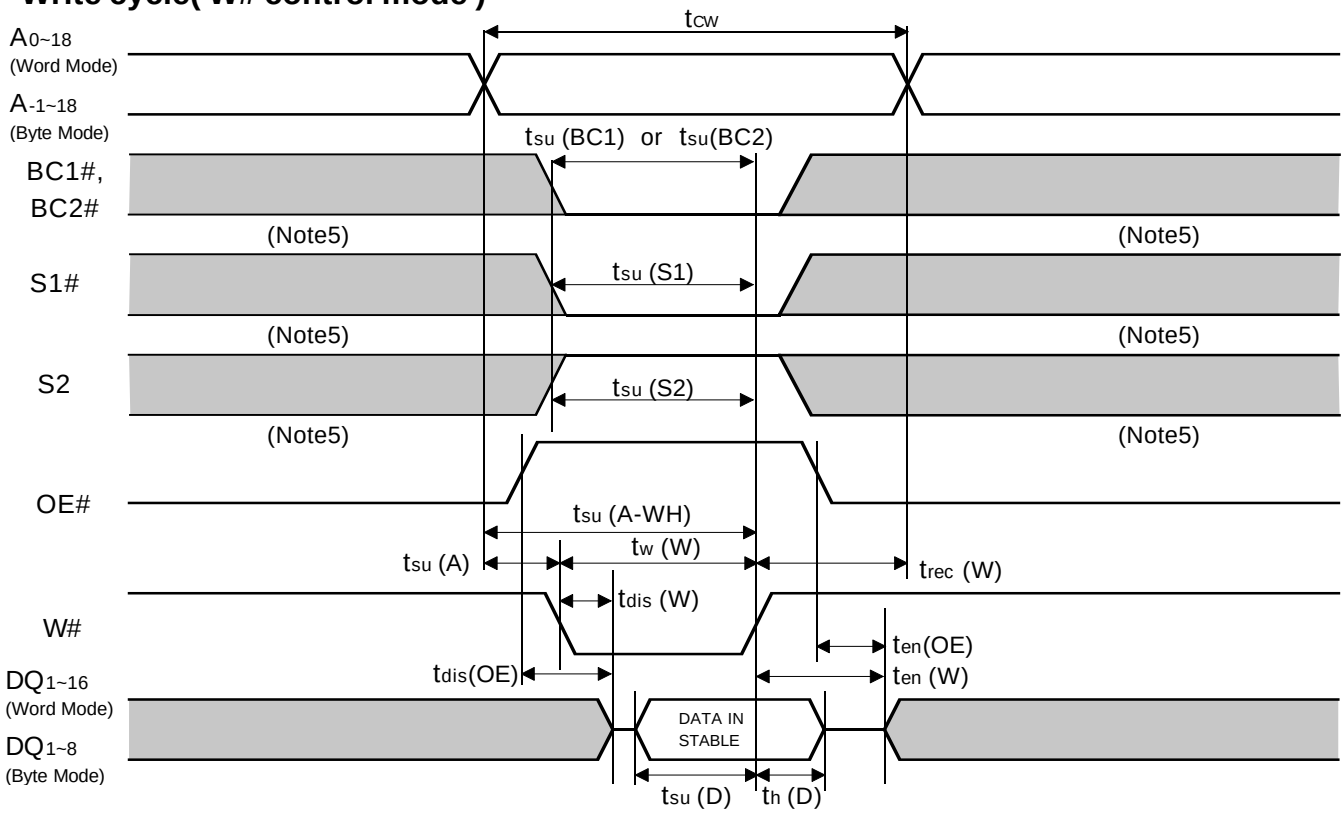
BYTE#



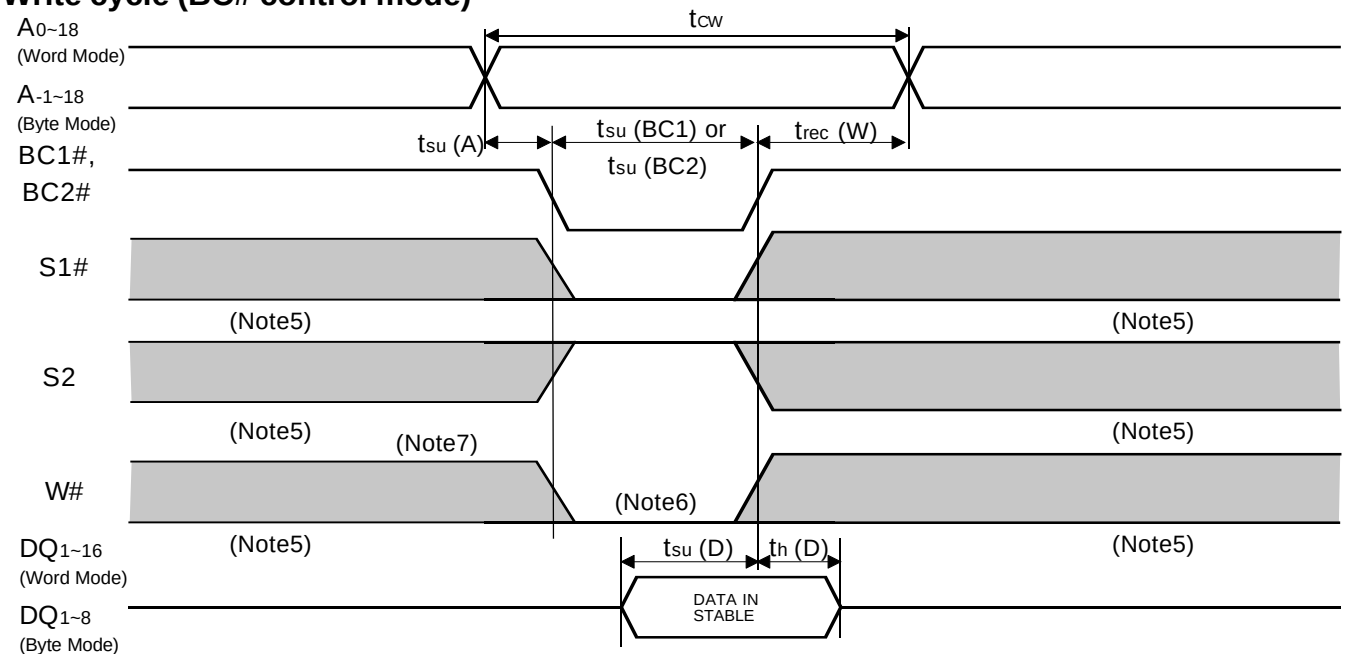
Read cycle



Write cycle(W# control mode)

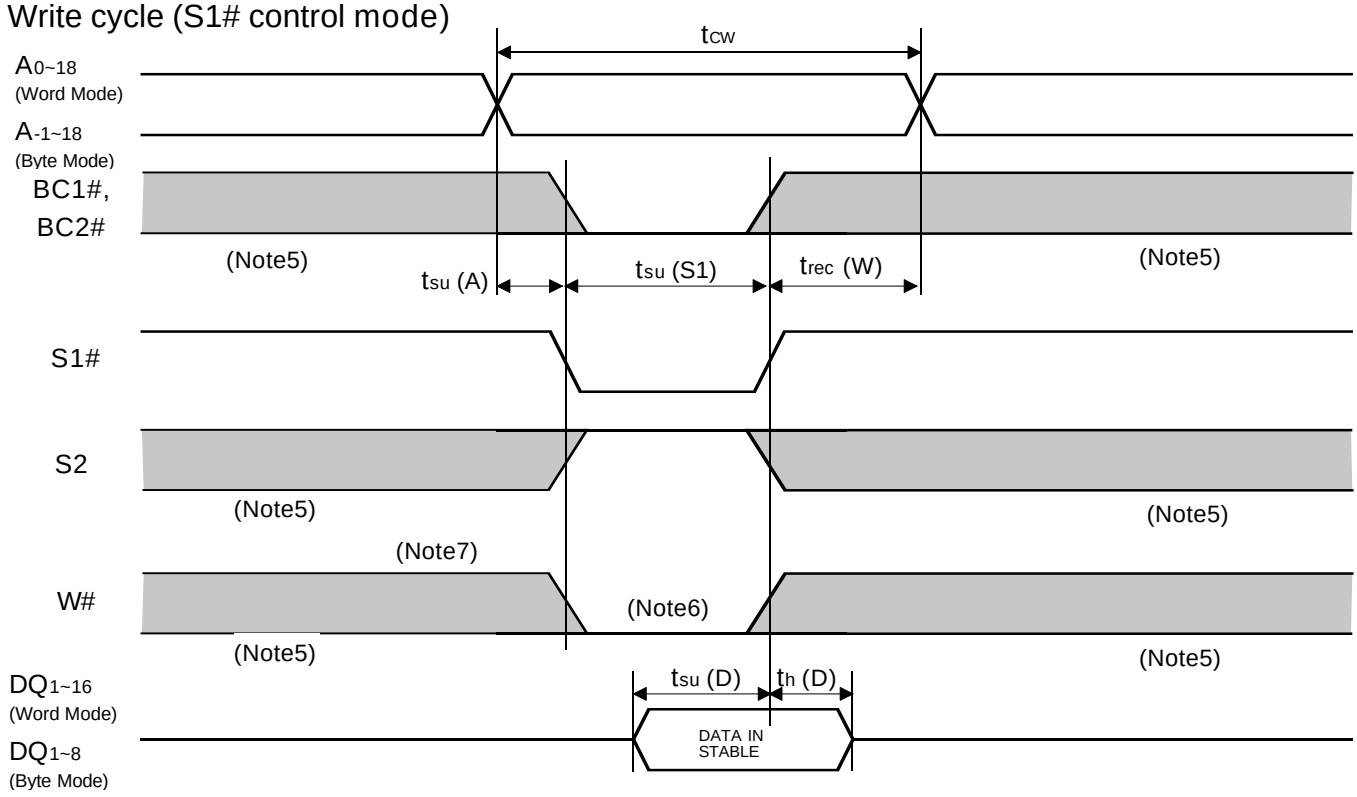


Write cycle (BC# control mode)

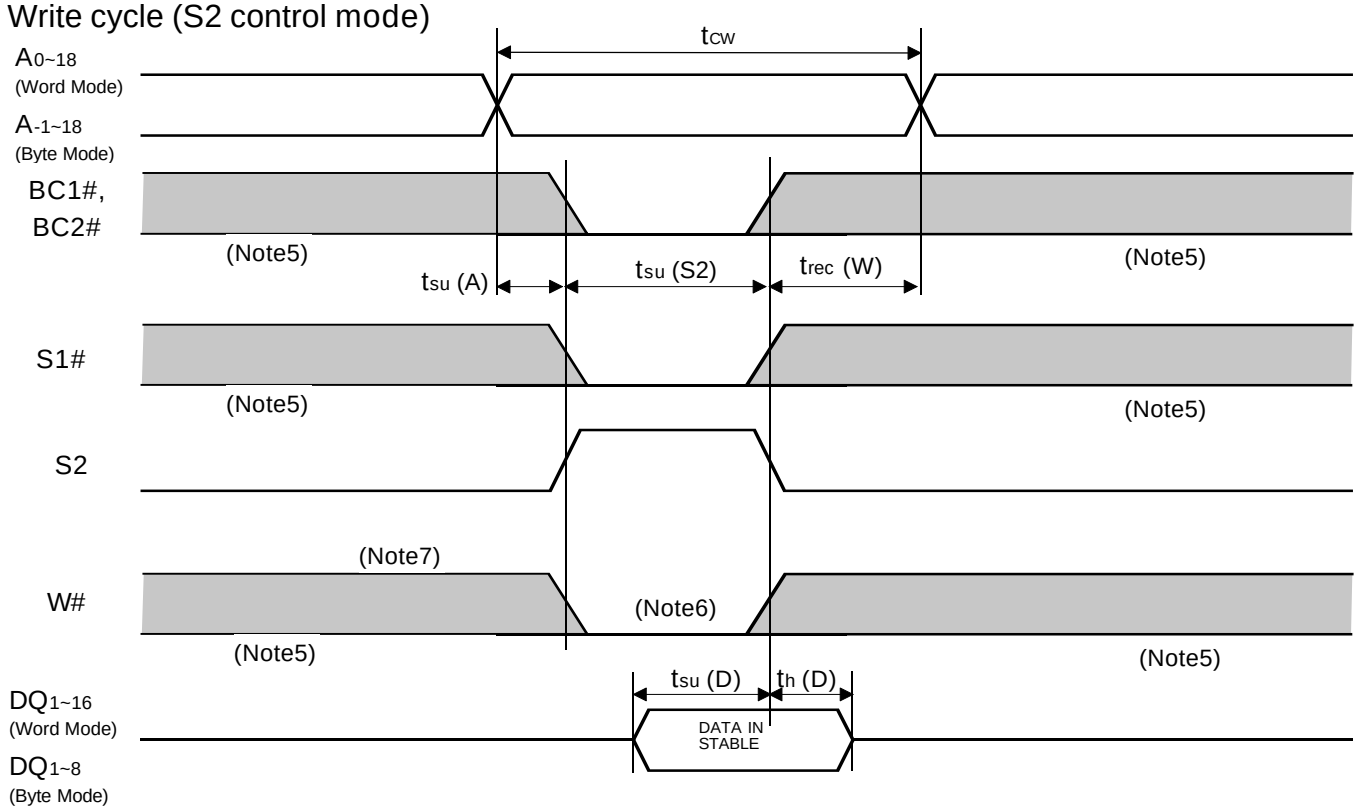


Note 5: Hatching indicates the state is "don't care".
Note 6: A Write occurs during S1# low, S2 high overlaps BC1# and/or BC2# low and W# low.
Note 7: When the falling edge of W# is simultaneously or prior to the falling edge of BC1# and/or BC2# or the falling edge of S1# or rising edge of S2, the outputs are maintained in the high impedance state.
Note 8: Don't apply inverted phase signal externally when DQ pin is in output mode.

Write cycle (S1# control mode)



Write cycle (S2 control mode)



POWER DOWN CHARACTERISTICS

(1) ELECTRICAL CHARACTERISTICS (Ta=-40~85ºC, Vcc=2.7V~3.6V,unless otherwise noted)

Symbol	Parameter	Test conditions		Limits Min	Limits Typ	Limits Max	Units
Vcc (PD)	Power down supply voltage			2.0			V
VI (BC)	Byte control input BC1# & BC2#			2.0			V
VI (S1#)	Chip select input S1#			2.0			V
VI (S2)	Chip select input S2					0.2	V
Icc (PD)	Power down supply current	**Vcc=2.0V** (1) S1# ≥ Vcc - 0.2V, BYTE# ≥ Vcc - 0.2V or ≤ 0.2V other inputs = 0 ~ Vcc (2) S2 ≤ 0.2V , BYTE# ≥ Vcc - 0.2V or ≤ 0.2V other inputs = 0 ~ Vcc (3) BC1# and BC2# ≥ Vcc - 0.2V S1# ≤ 0.2V, S2 ≥ Vcc - 0.2V BYTE# ≥ Vcc - 0.2V or ≤ 0.2V other inputs = 0 ~ Vcc	~ +25°C	-	0.2	3.0	µA
			~ +40°C	-	0.4	6.0	
			~ +70°C	-	-	30	
			~ +85°C	-	-	60	

Note 9: Typical parameter of Icc(PD) indicates the value for the center of distribution at 2.0V, and not 100% tested.

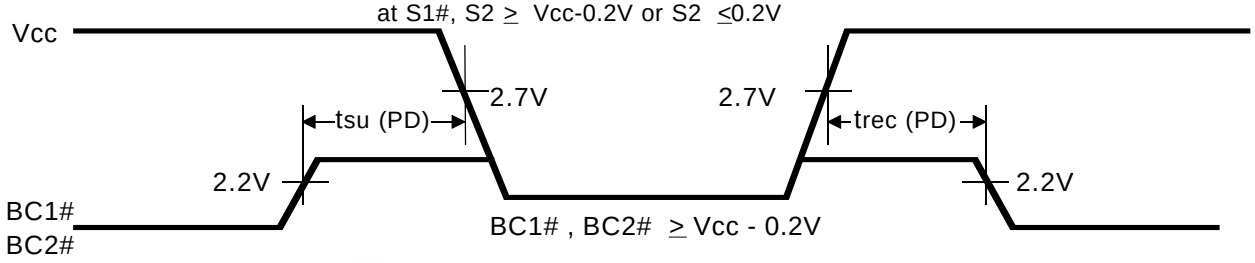
(2) TIMING REQUIREMENTS

Symbol	Parameter	Test conditions	Limits Min	Limits Typ	Limits Max	Units
tsu (PD)	Power down set up time		0			ns
trec (PD)	Power down recovery time		5			ms

(3) TIMING DIAGRAM

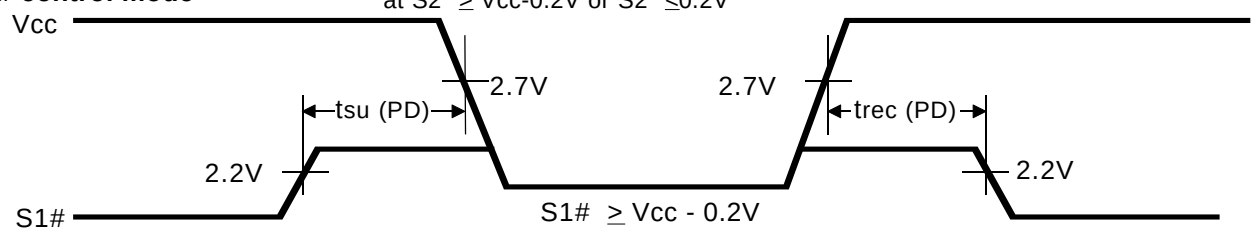
BC# control mode

note10:On the BC# control mode, the level of S1# and S2 must be fixed at S1#, S2 ≥ Vcc-0.2V or S2 ≤0.2V

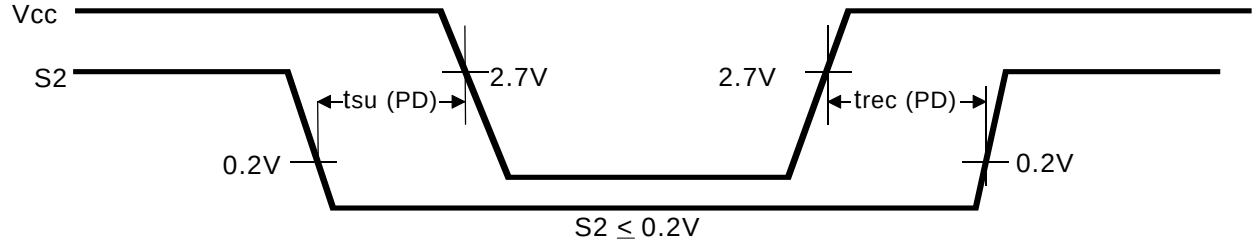


S1# control mode

note11:On the S1# control mode, the level of S2 must be fixed at S2 ≥ Vcc-0.2V or S2 ≤0.2V



S2 control mode



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